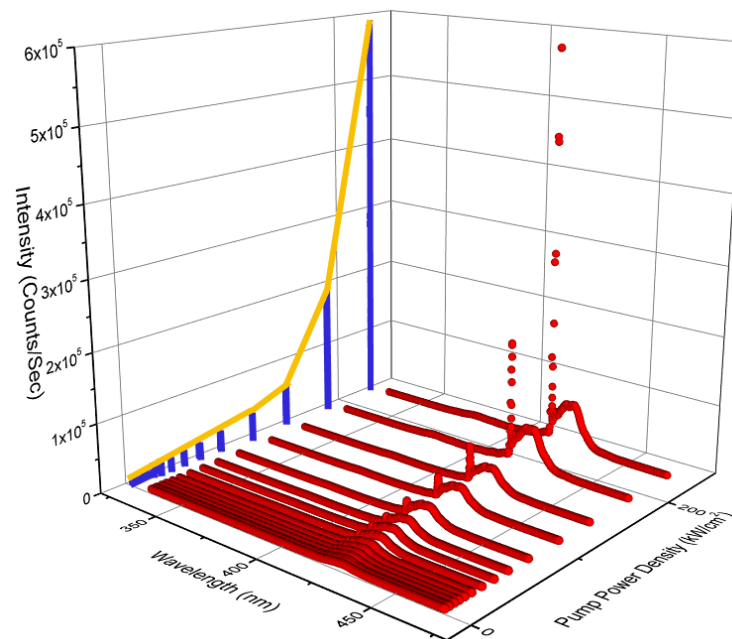
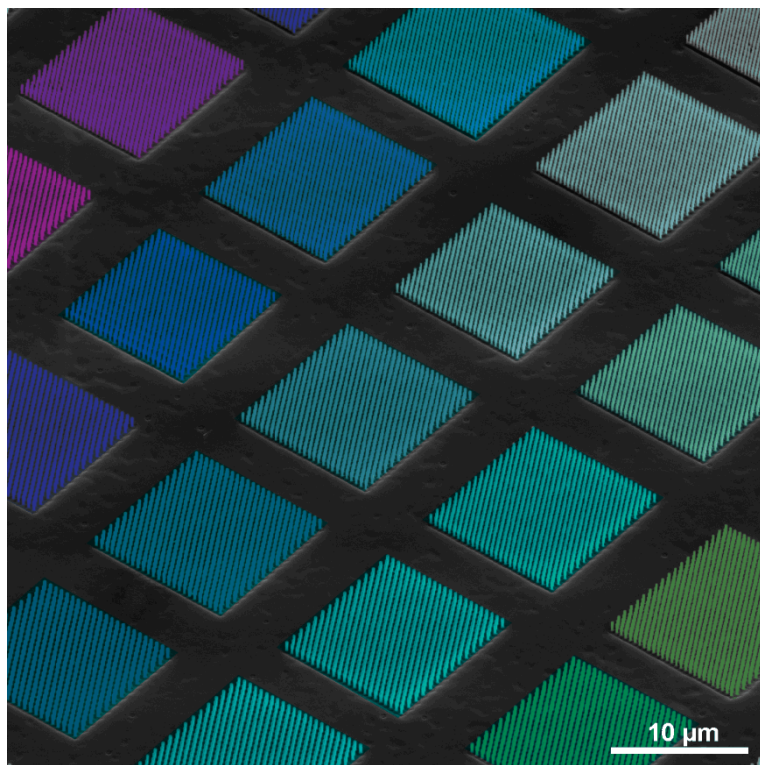


Tunable Blue-Violet III-Nitride Nanowire Photonic Crystals

SAND2013-4688C

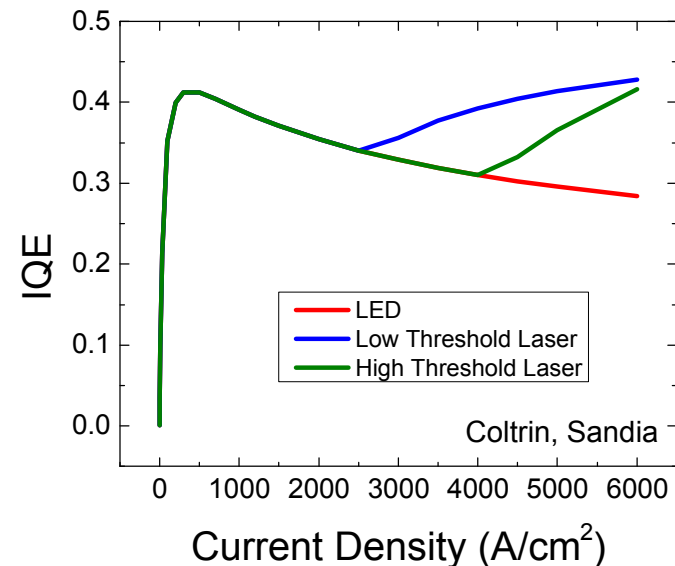
Jeremy B. Wright, Sheng Liu, Alexander Benz, George T. Wang, Qiming Li, Daniel D. Koleske, Ping Lu, Huiwen Xu, Luke Lester, Ting S. Luk, Igal Brener, Ganapathi S. Subramania



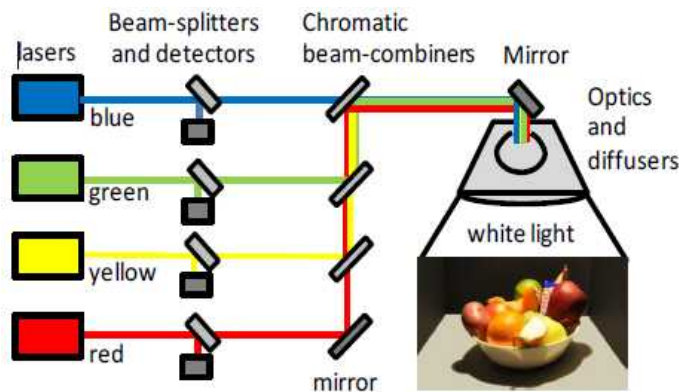
This work was supported by Sandia's Solid-State Lighting Science Energy Frontier Research Center, sponsored by the Department of Energy Office of Science. This work was performed, in part, at the Center for Integrated Nanotechnologies, a U.S. Department of Energy, Office of Basic Energy Sciences user facility. Sandia National Laboratories is a multi-program laboratory managed and operated by Sandia Corporation, a wholly owned subsidiary of Lockheed Martin Corporation, for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-AC04-94AL85000.

Why lasers in solid state lighting?

- The “efficiency droop”
 - InGaN LEDs exhibit a decrease in efficiency at high drive currents
 - limits the operating current density
 - increases the cost per lumen



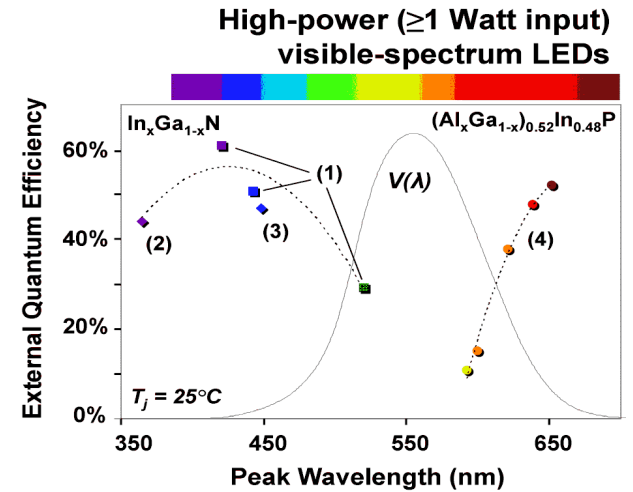
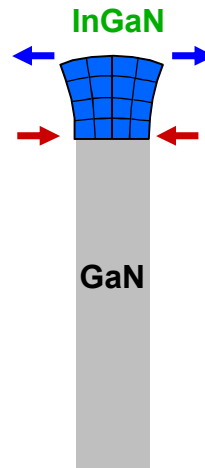
4-Color Laser Illuminant



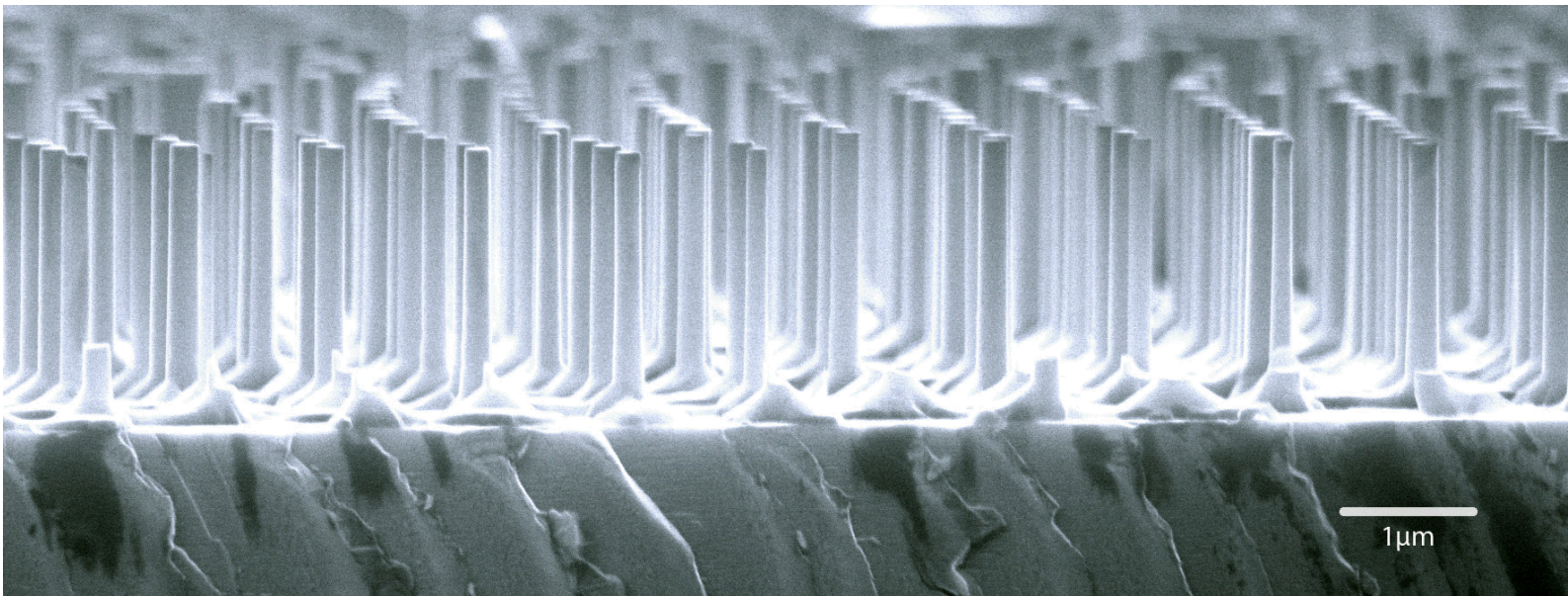
A. Neumann et al., "Four-color laser white illuminant demonstrating high color-rendering quality," *Opt. Express*, vol. 19, pp. A982-A990, 2011.

Why Nanowires for Lasing?

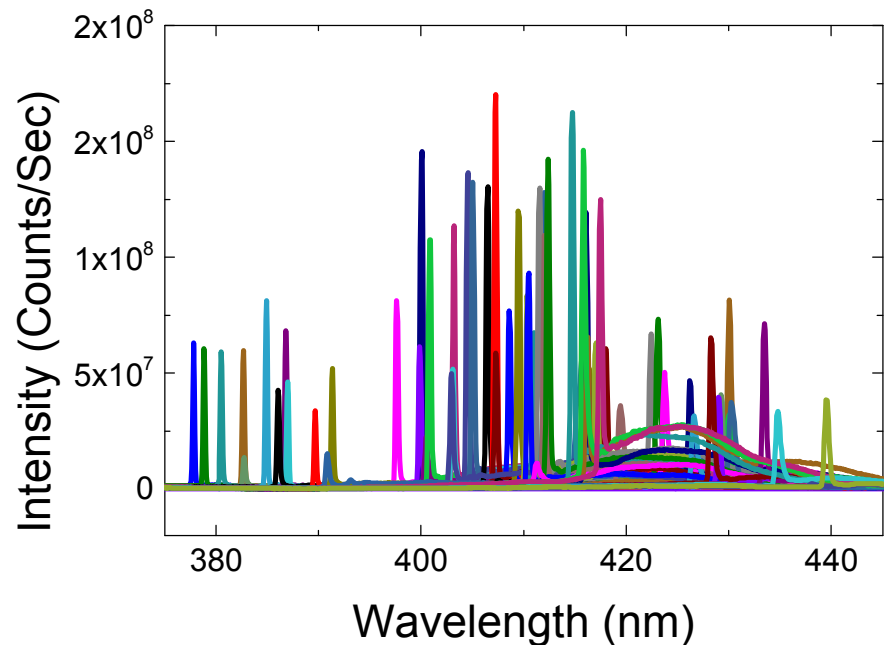
- Reduced strain
 - Greater range of alloy compositions
- Easily integrated into two-dimensional arrays



M. Krames, Philips Lumileds

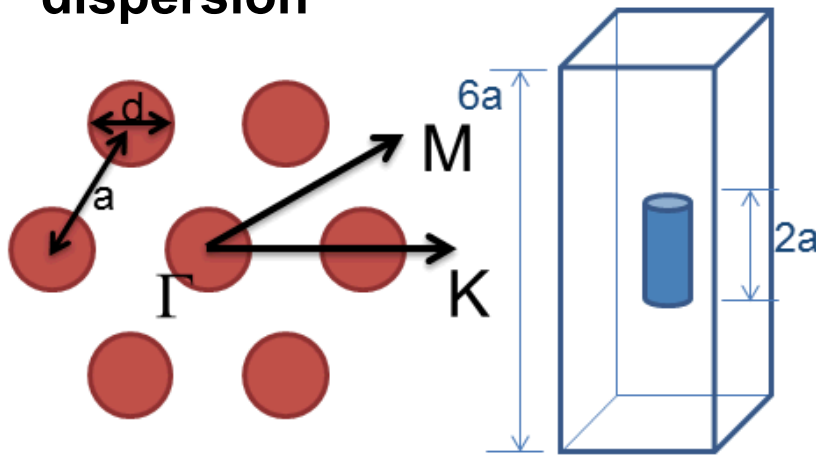


- **Design: Slow Group Velocity Modes**
- **Fabrication: Top-down Nanowire Photonic Crystals**
- **Optical Characterization and Results**

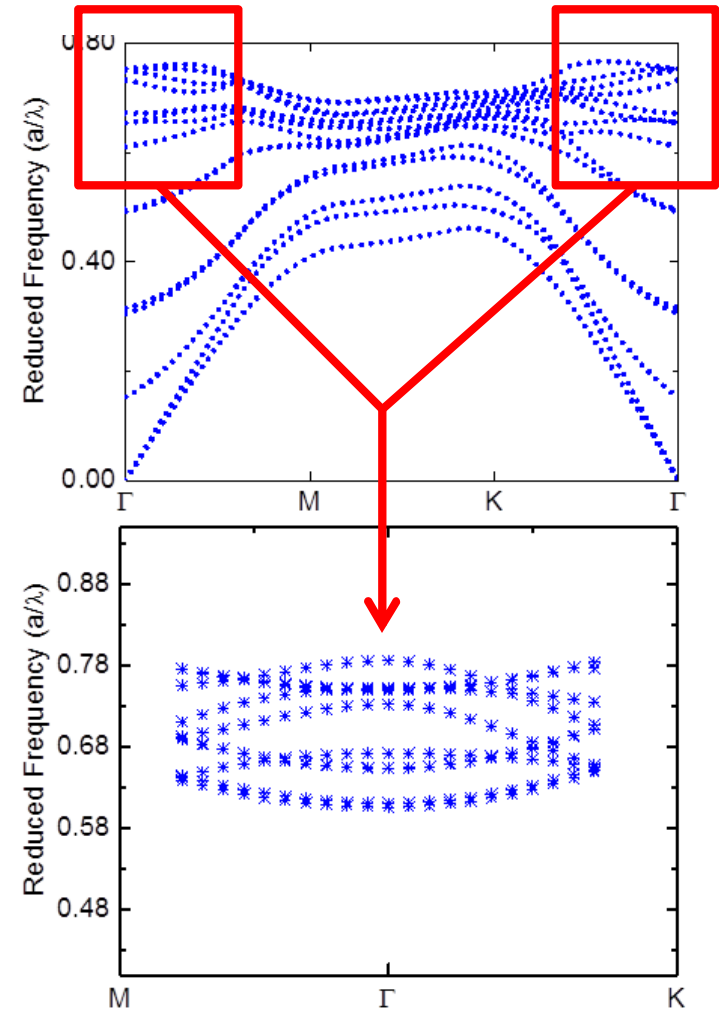


Designing vertically emitting photonic crystal lasers.

- We desire low group velocity
 - enhances the light matter interaction
 - forms standing waves within the gain medium
 - First described by Sakoda (1999)
- We designed high order bands designed to have low dispersion



Plane Wave Expansion Super Cell



Fabrication | Growth of III-N active material

- 4 μ m GaN bufferlayer
- 2% In Underlayer
- 5 MQW InGaN/GaN near the surface

20nm GaN cap layer

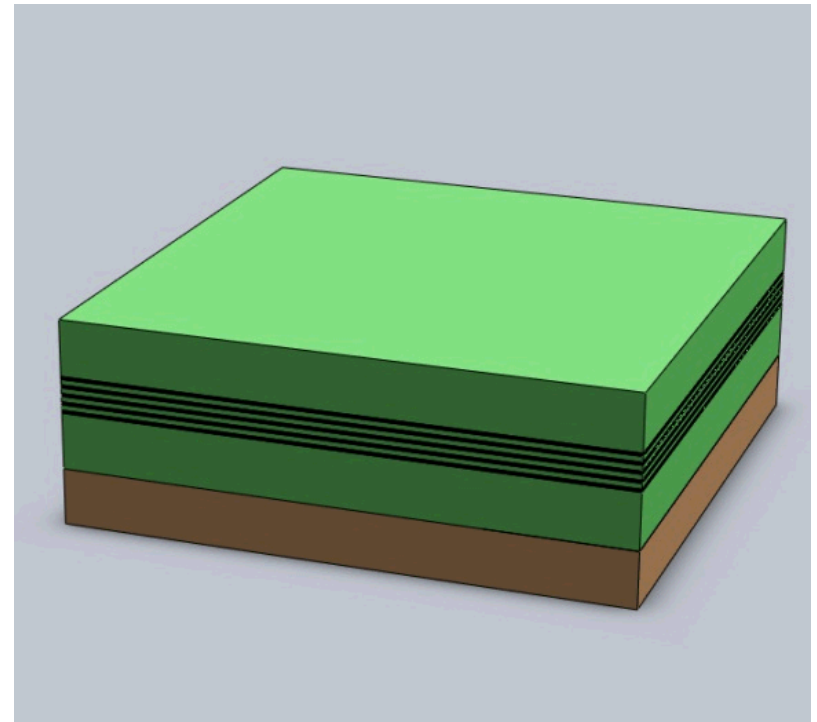
5X MQW Stack

120nm InGaN Underlayer

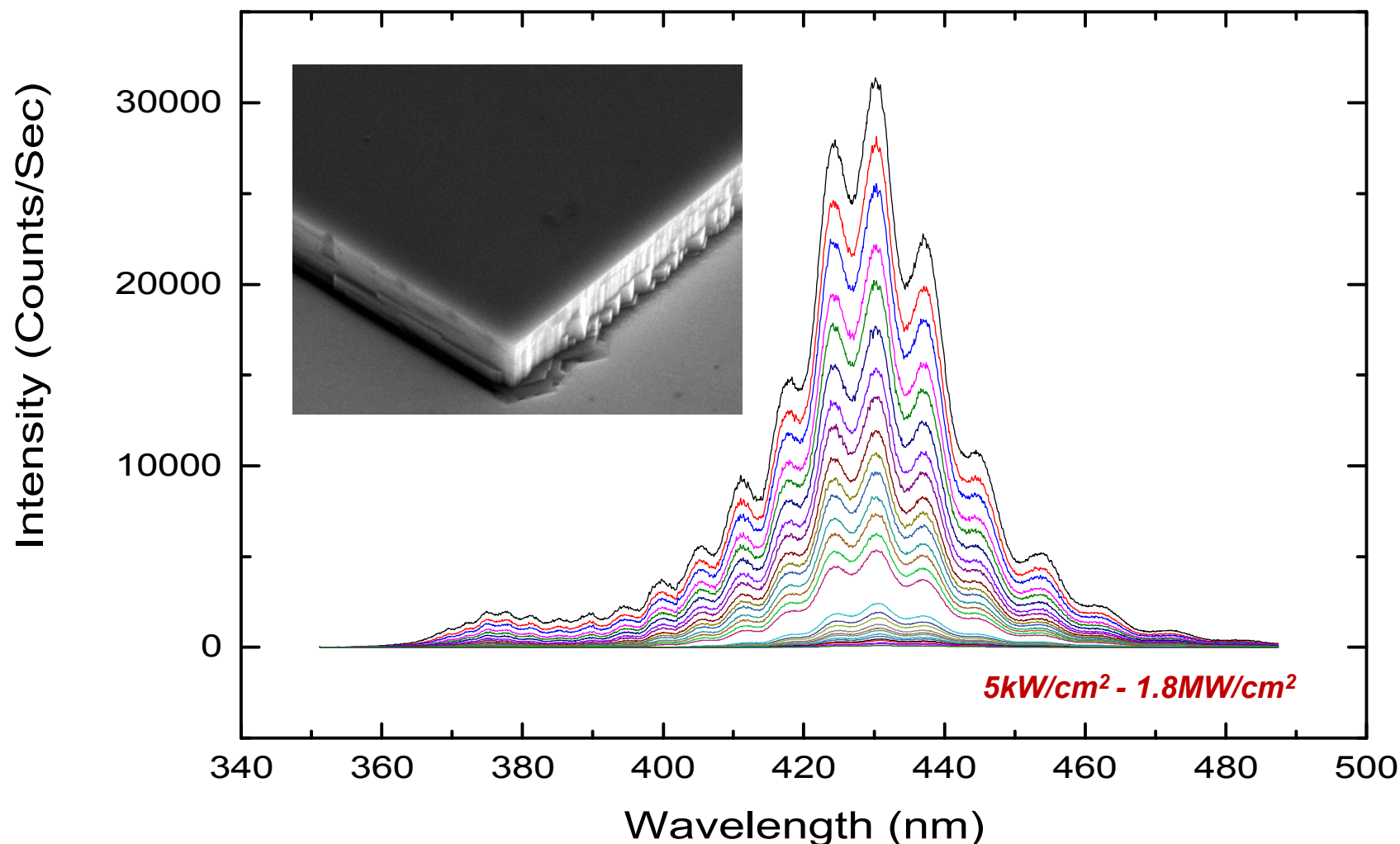
Bottom GaN Layer

4 μ m GaN Bufferlayer

Sapphire Substrate

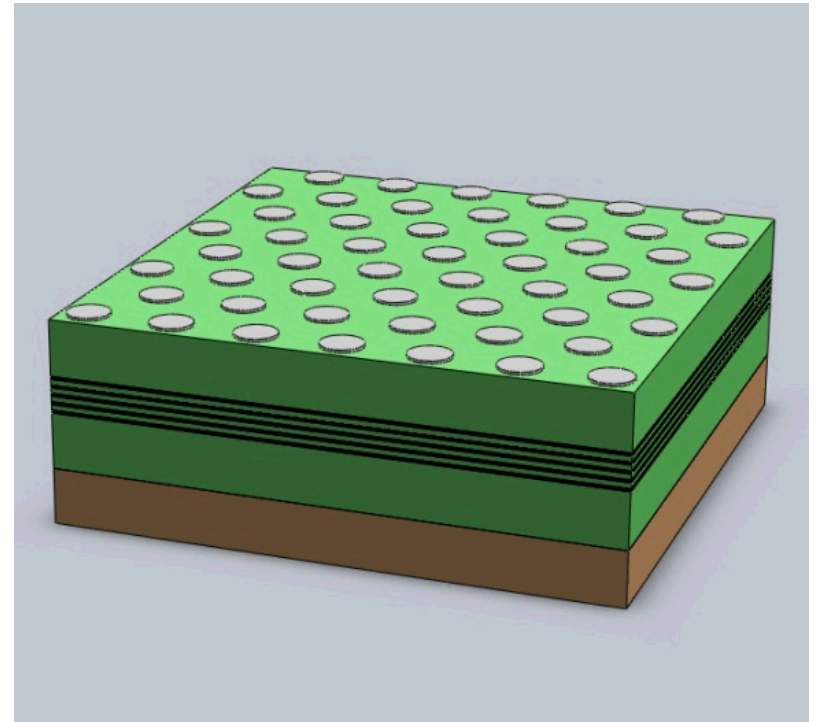
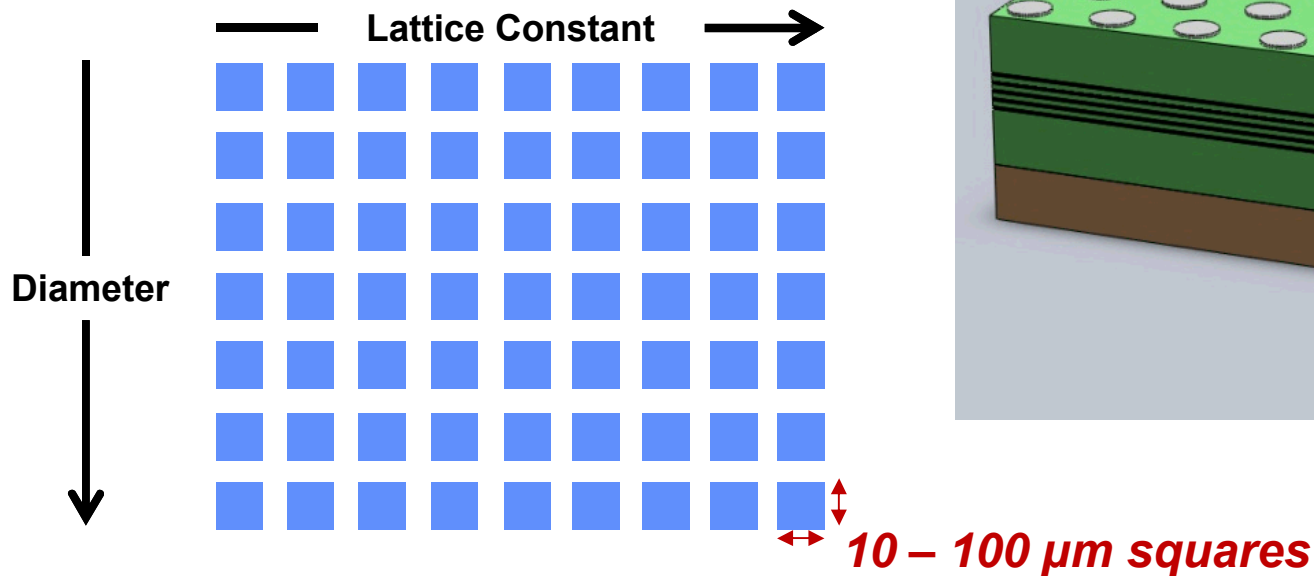


Photoluminescence from a non-etched reference region.



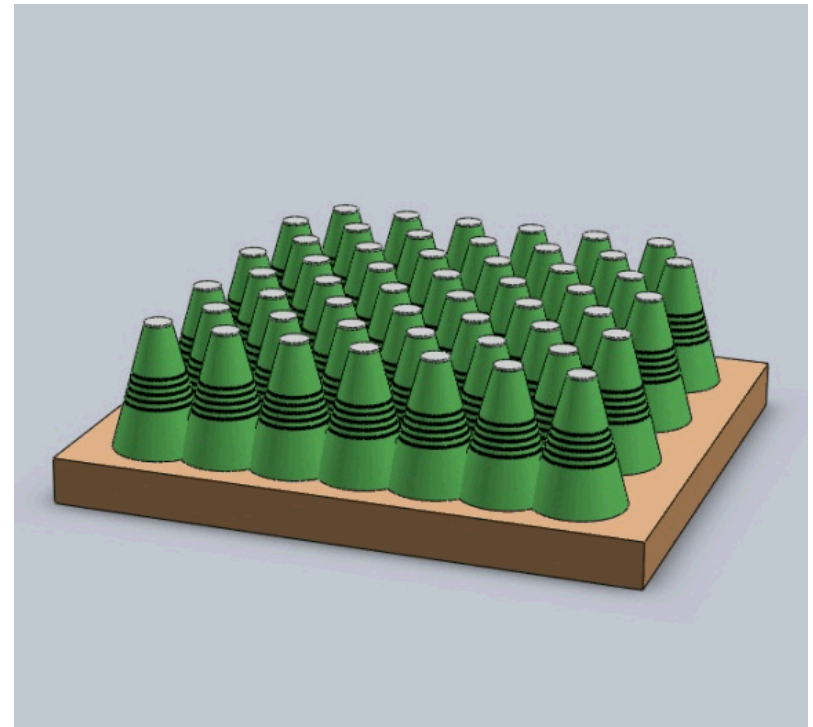
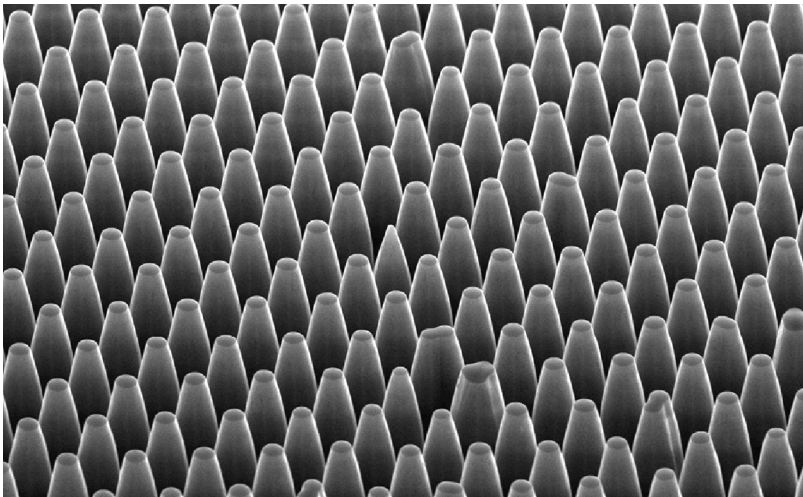
Fabrication | Patterning of 2DPC using e-beam

- E-beam Patterning
- Triangular Lattice of Ni Dots
- 9x7 array



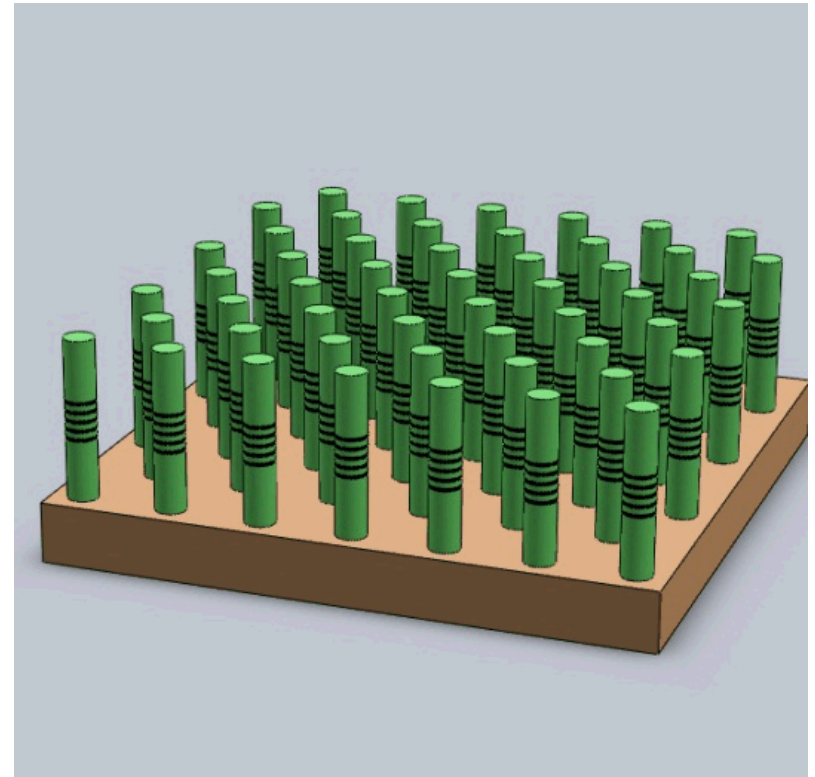
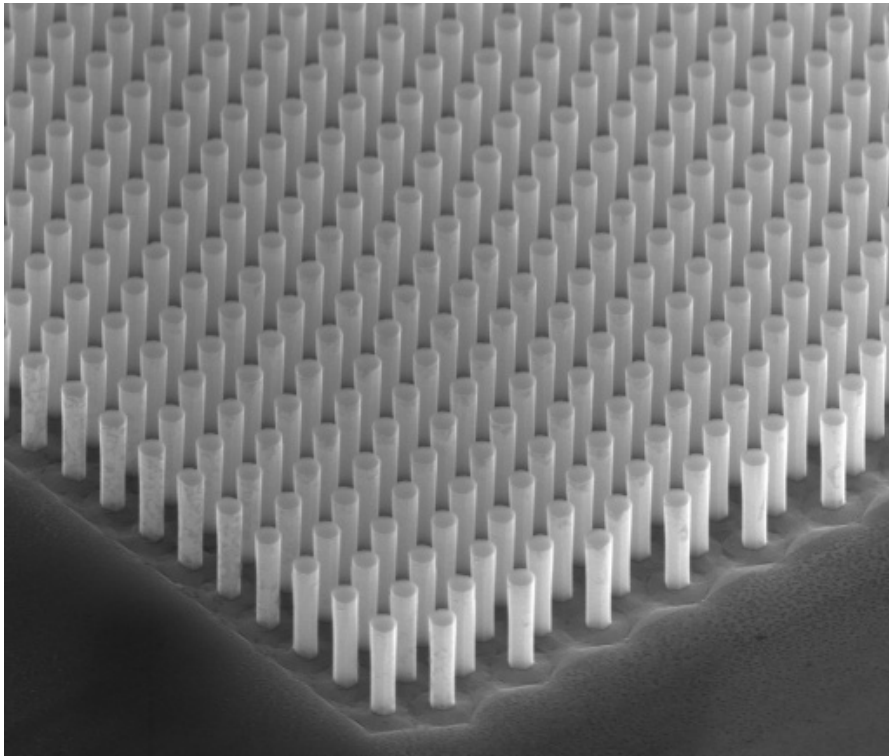
Fabrication | top-down 2-step etch process

- Same process as our top-down nanowires
- Dry (ICP) followed by wet (KOH) process



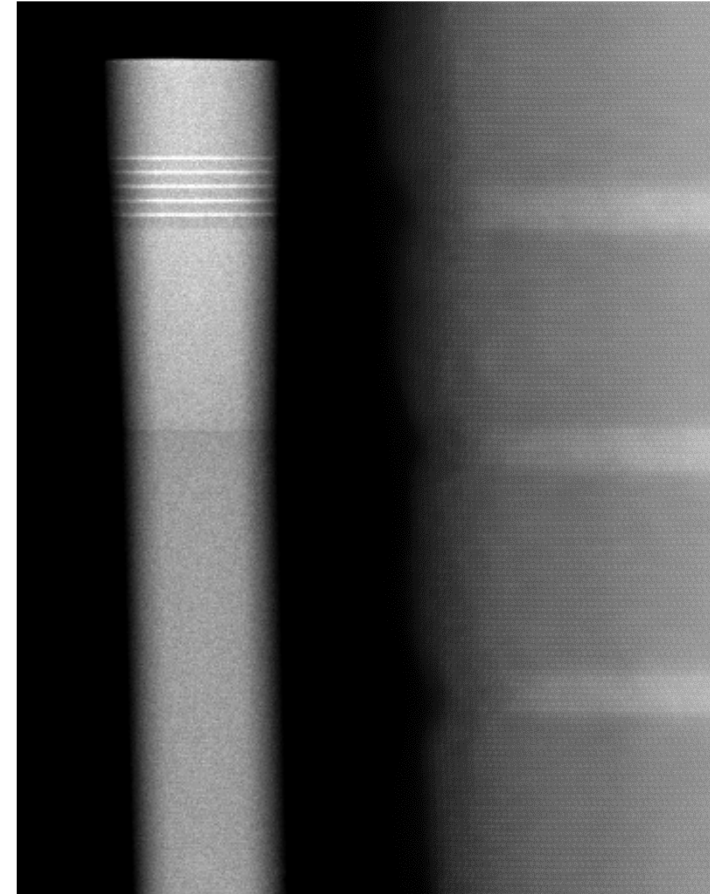
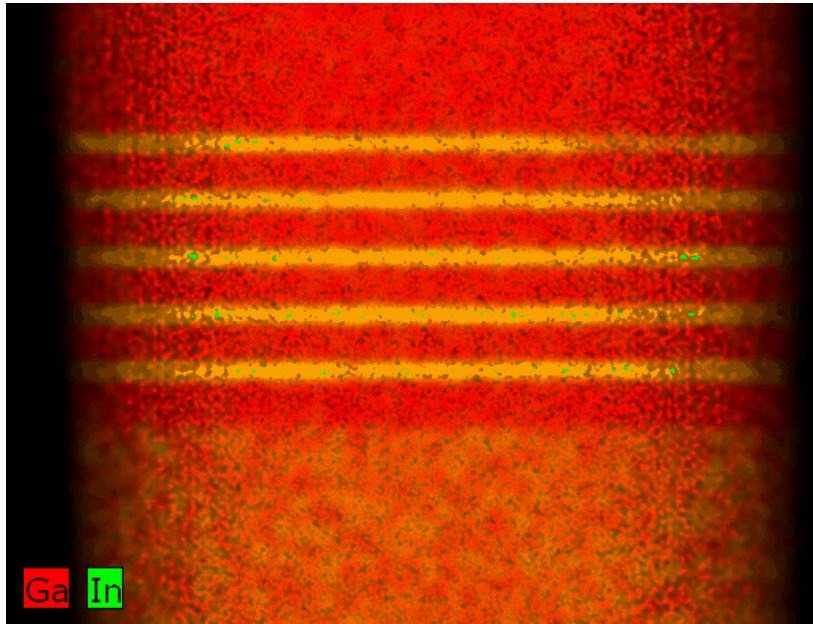
Li, Q. et al. Optical performance of top-down fabricated InGaN/GaN nanorod light emitting diode arrays. *Opt. Express* **19**, 25528-25534 (2011).
Li, Q. et al. Single-mode GaN nanowire lasers. *Opt. Express* **20**, 17873-17879 (2012).

Fabrication | Ordered arrays of anisotropic nanowires



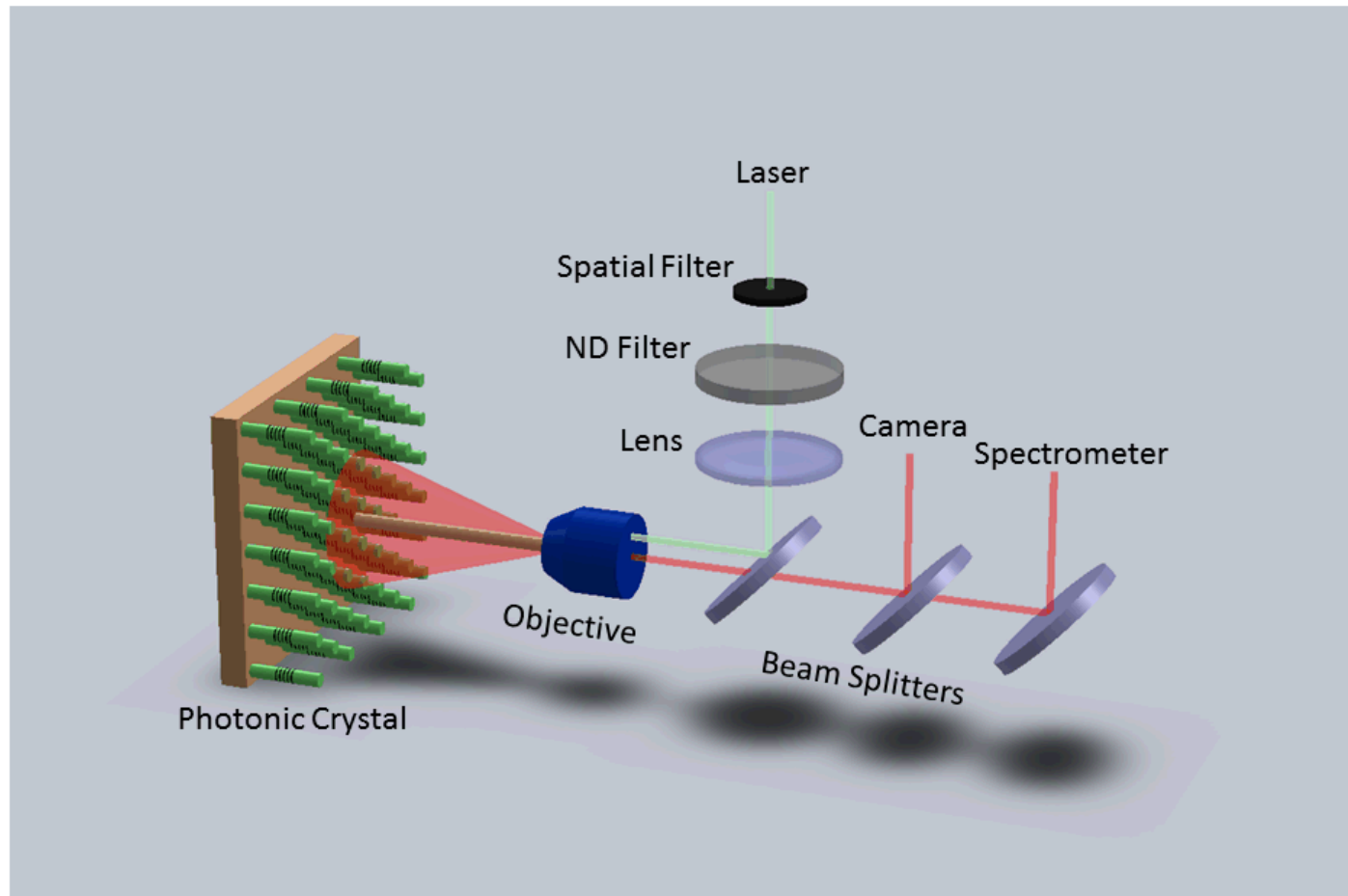
TEM of a single nanowire taken from an array

- 5x MQW InGaN Emission Centered at 430nm
- 2% In underlayer
- Slight taper from the InGaN quantum wells



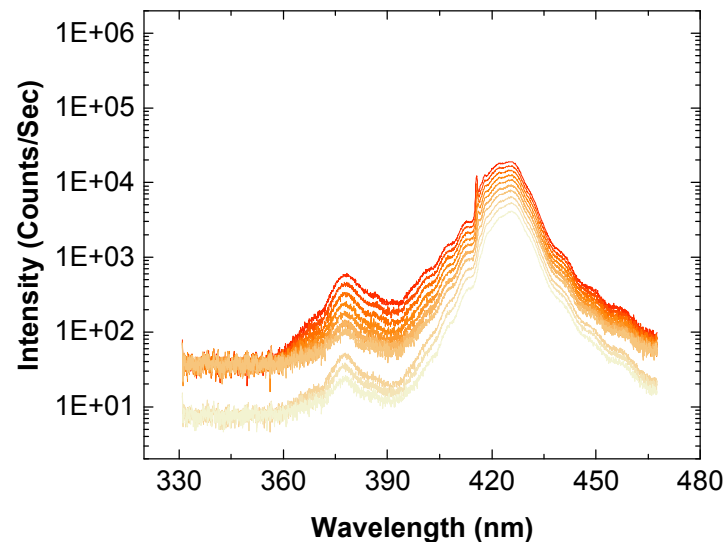
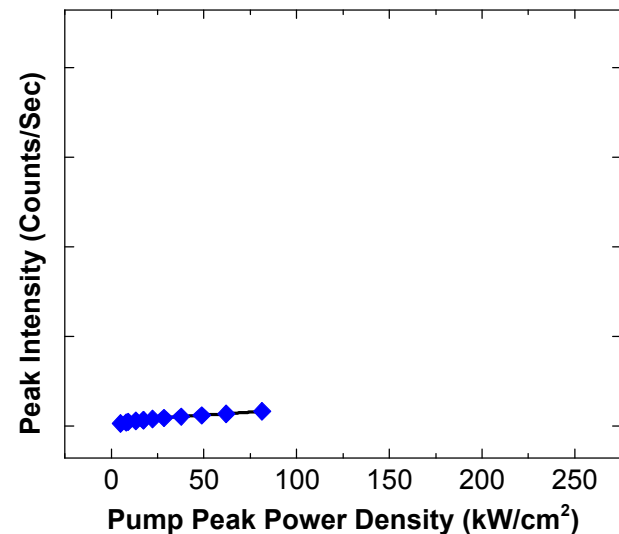
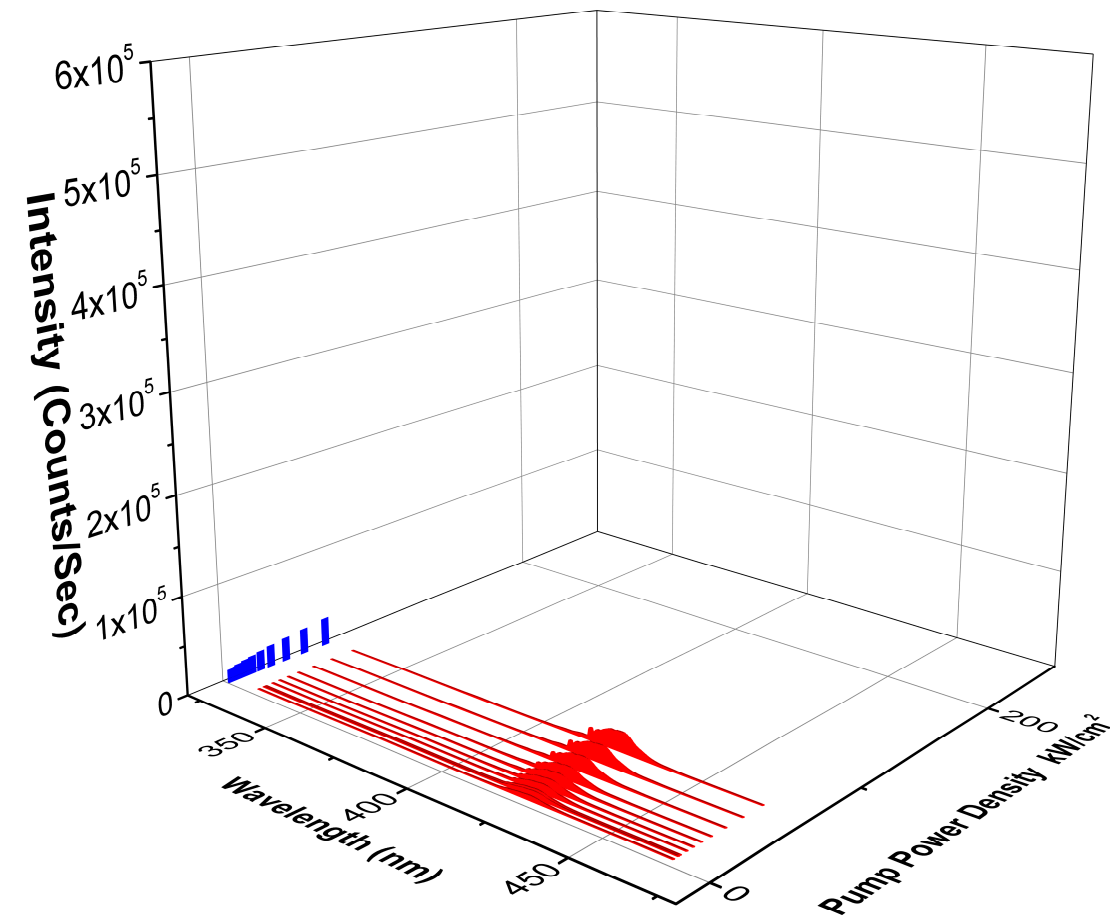
Ping Lu, Sandia

micro-Photoluminescent Optical Characterization



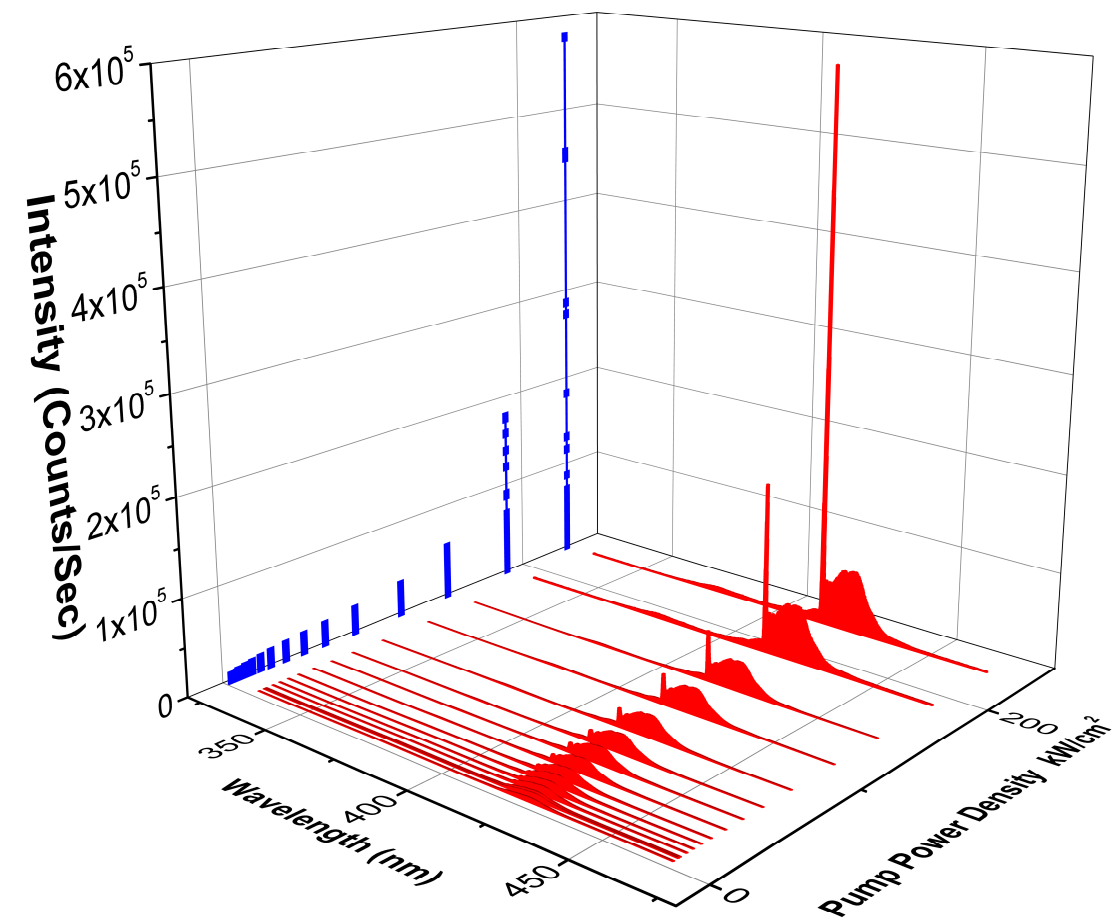
Pump spot is tunable in size and power density.

Below Threshold Spectra of a 2DPC Laser

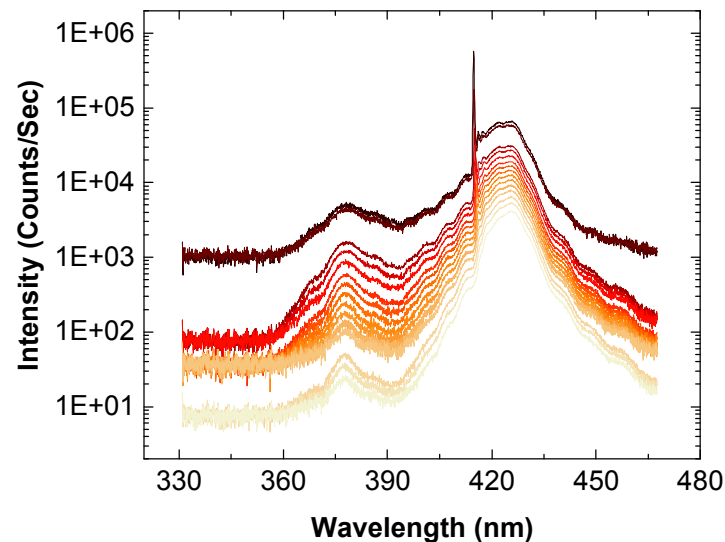
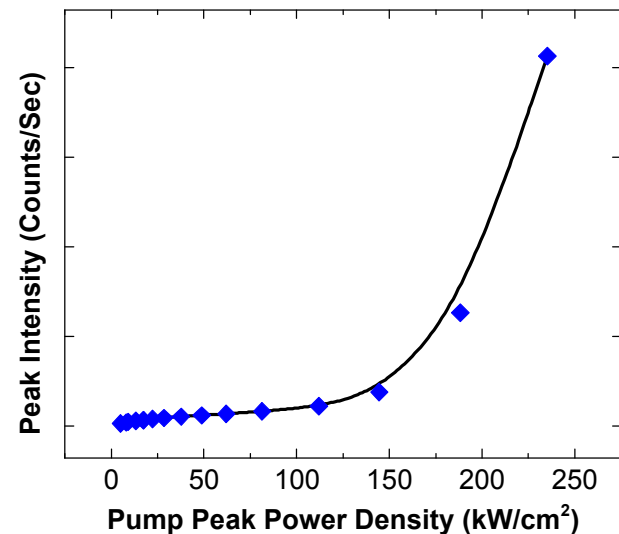


Array Element Dimensions: $d=145$ nm and $a=320$ nm.

Above Threshold Spectra of a 2DPC Laser

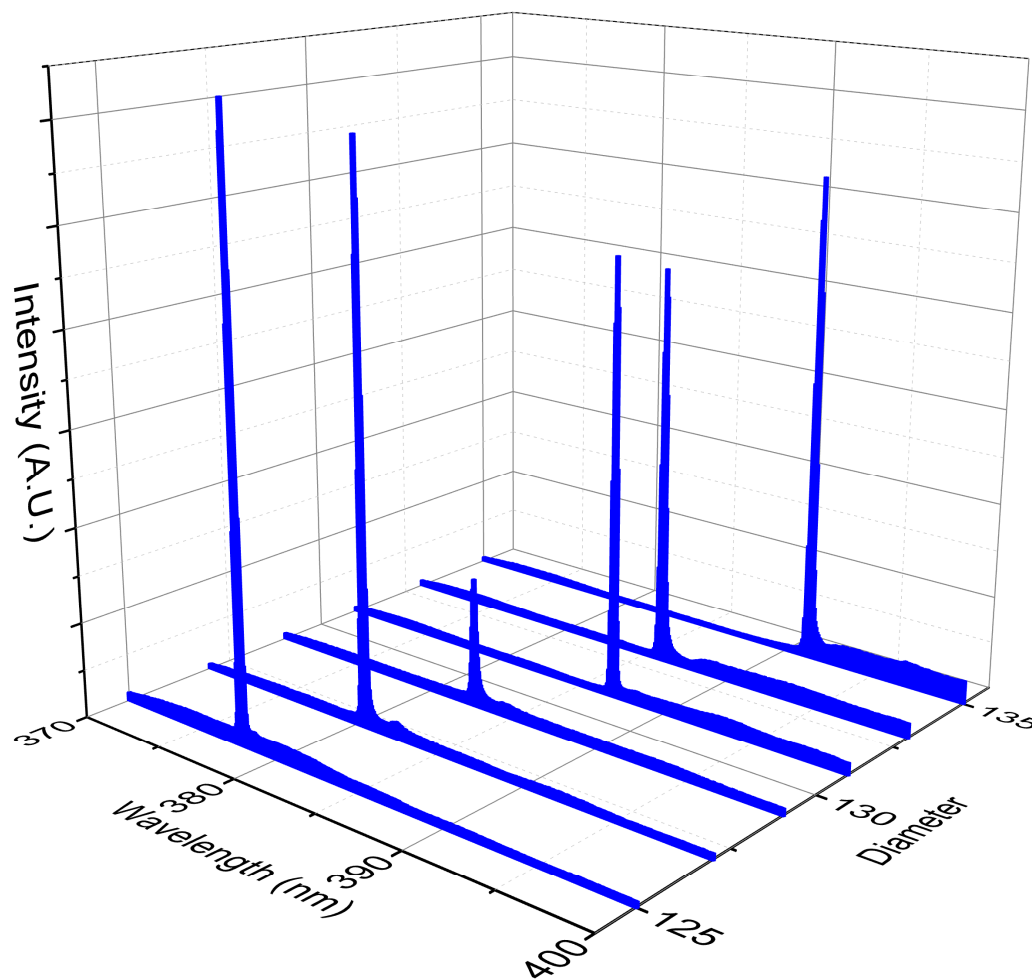


Array Element Dimensions: $d=145 \text{ nm}$ and $a=320 \text{ nm}$.



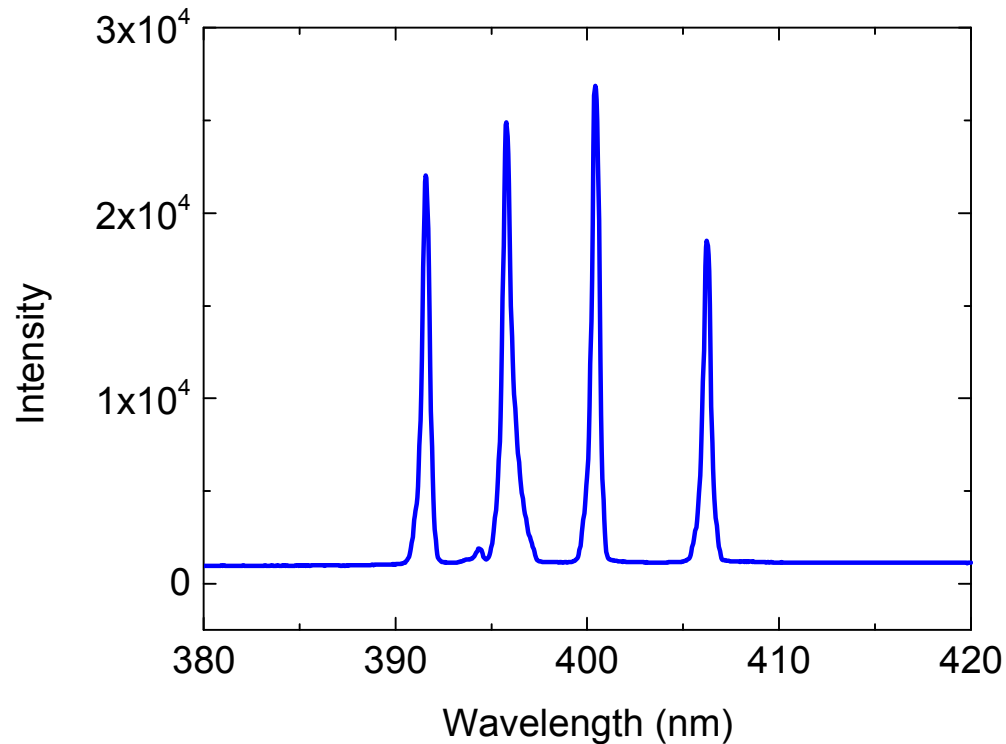
Diameter Dependent Emission for a given Lattice Constant

$a =$	290	295	300
			
		125	
			
		127	
			
		129	
			
		131	
			
		135	

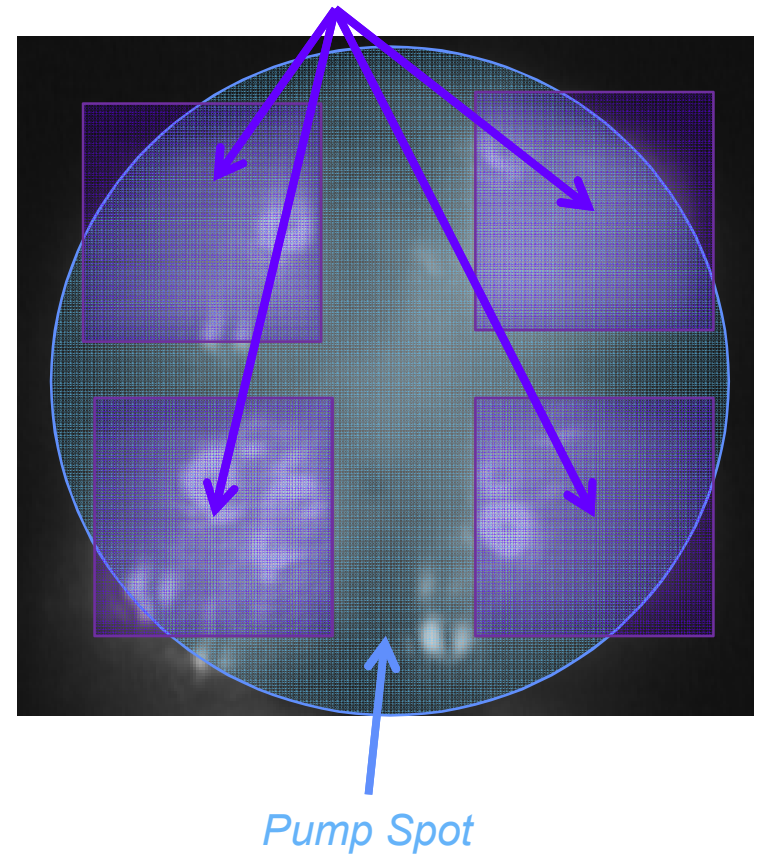


Multiple Laser Pixels Coexcited

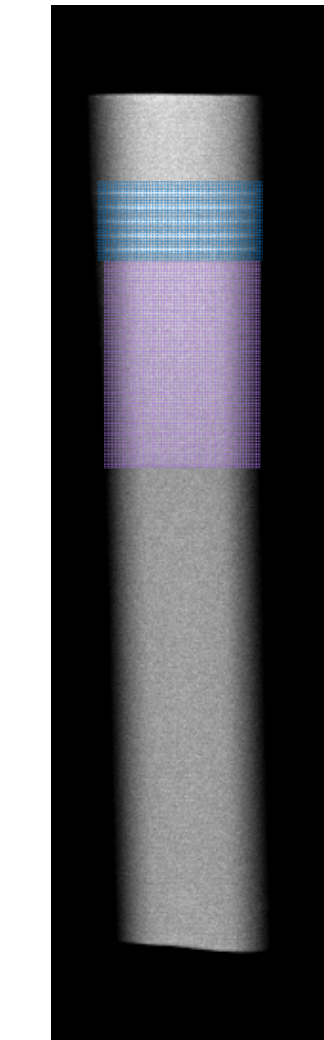
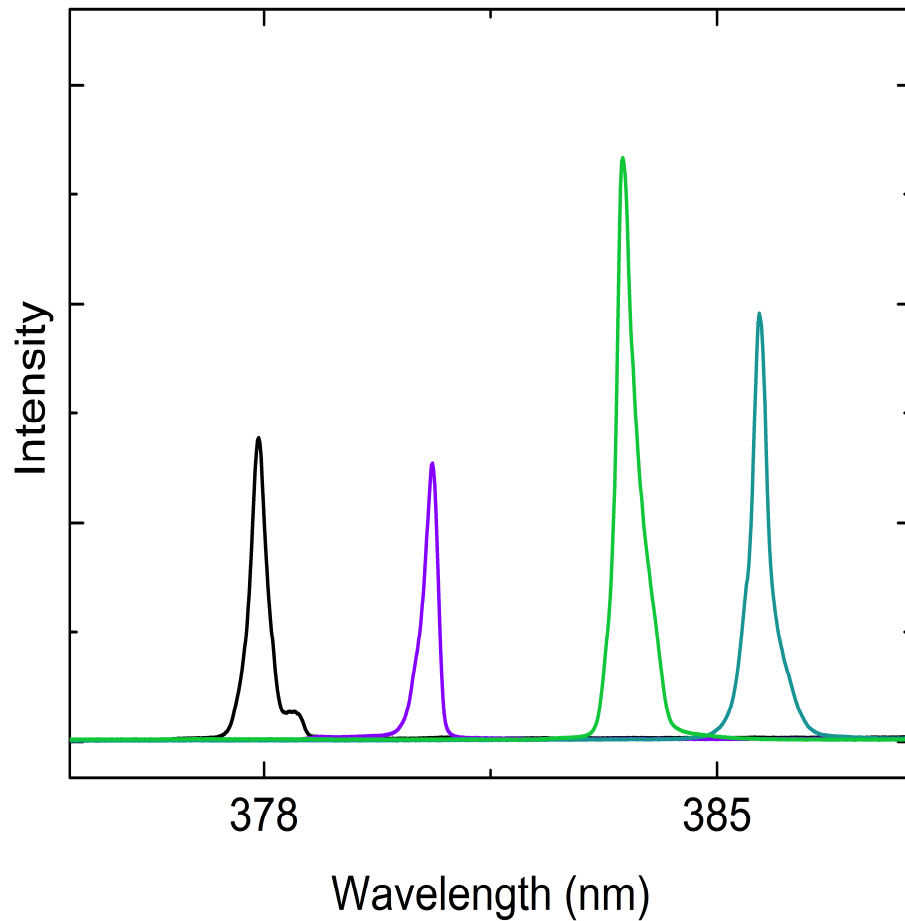
Emission from 4 adjacent laser pixels.



Photonic Crystal Laser Pixels



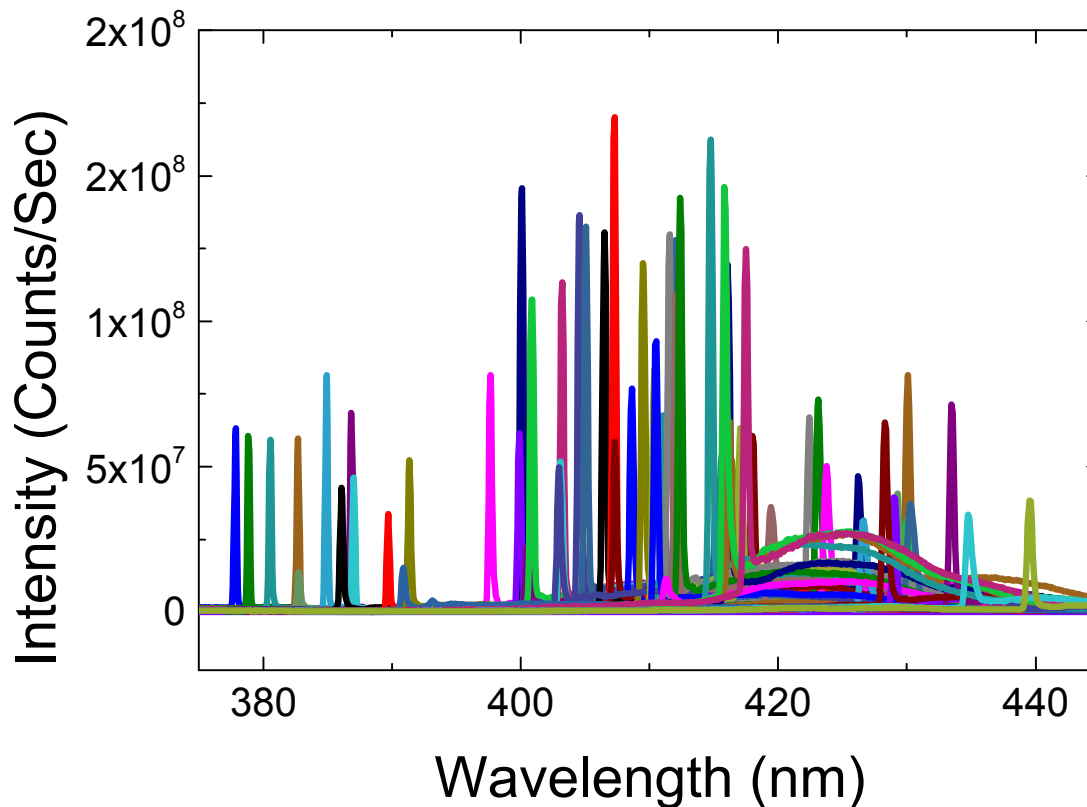
Gain from multiple sections



*MQW Gain
Section*

*Underlayer Gain
Section*

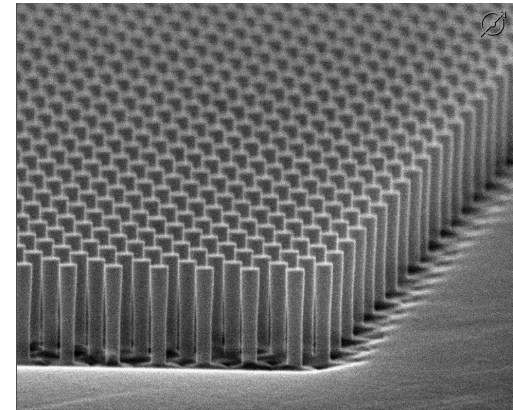
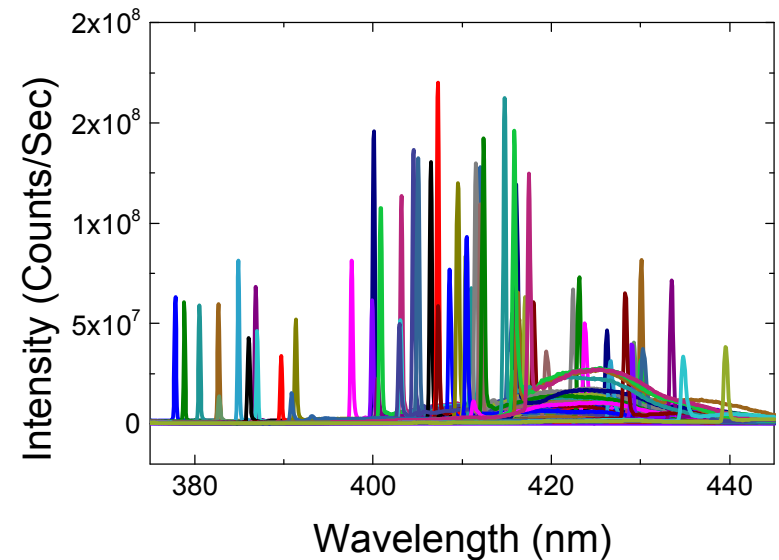
Multi-color Laser Array



- **Spectral Coverage from 380-440nm.**
- **Thresholds are reasonable compared to other optically pumped III-N nanowire devices. ($<500\text{kW}/\text{cm}^2$ for all devices)**

Summary

- **Fabricated laser arrays that span a broad spectral range**
 - Near-Vertical single-mode emitters
 - Thresholds are non-homogeneous but remain reasonable for optical pumping experiments
 - Possible to fabricate high density of emitters with a larger wavelength span
- **Technology implications**
 - Lasers for SSL
 - Displays and projectors

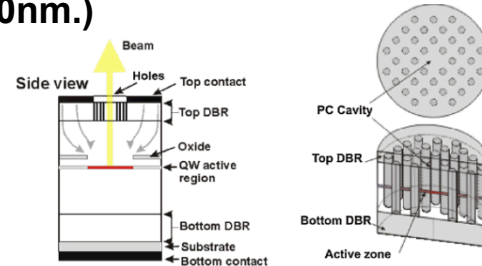
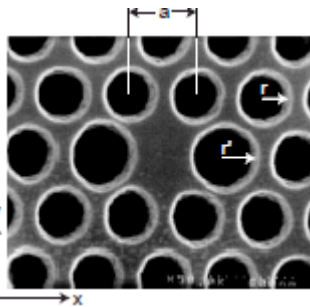


Thank you for your attention!

BACKUP MATERIAL

Previous Work

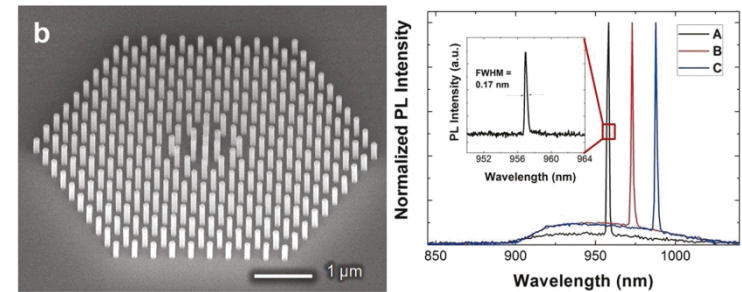
Most work on PCLs has been limited to
Phosphides, Antimonides, and Arsenides.
($\lambda > 700\text{nm.}$)



Ivanov et al...0268-1242_27_9_094010

Painter, O. et al. *Science* **284** (1999).

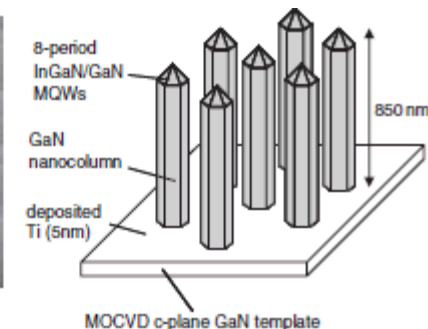
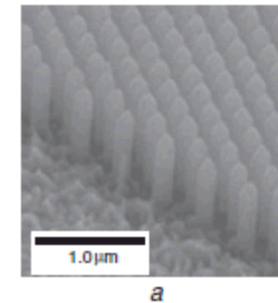
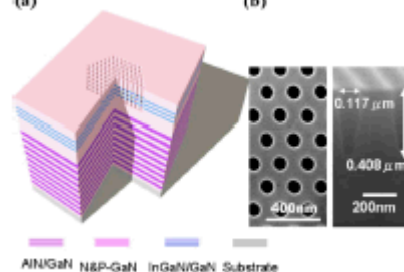
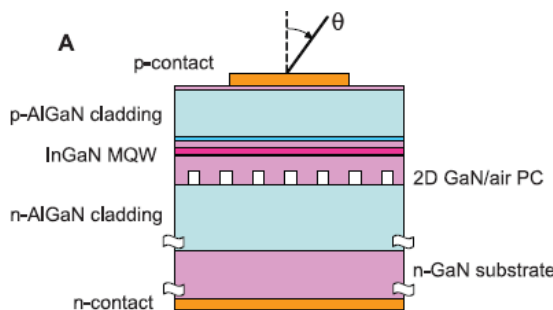
Previous tuning results limited to $< 30\text{nm}$



Scofield, A. C. et al. *Nano Lett.* **11**, (2011).

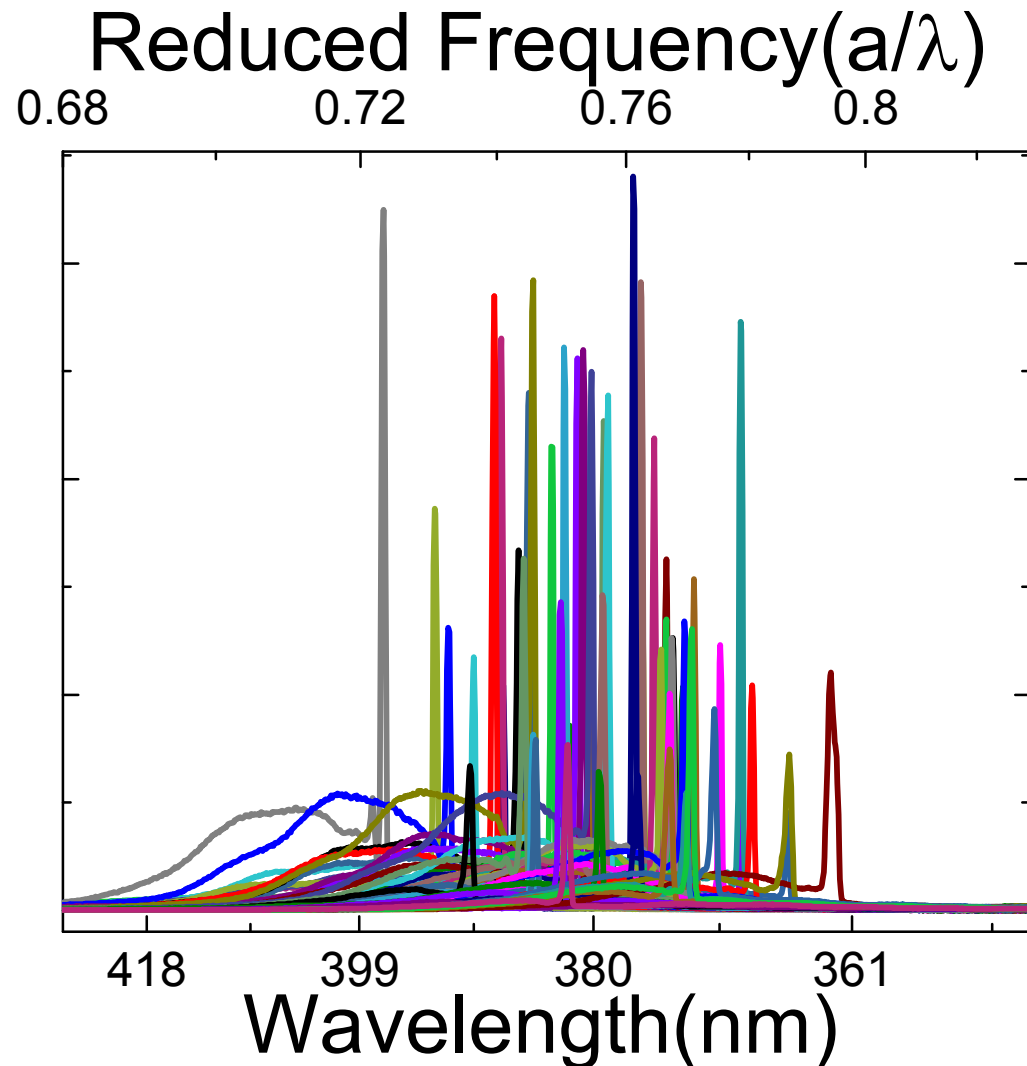
III-N difficult to fabricate or lack of tuning

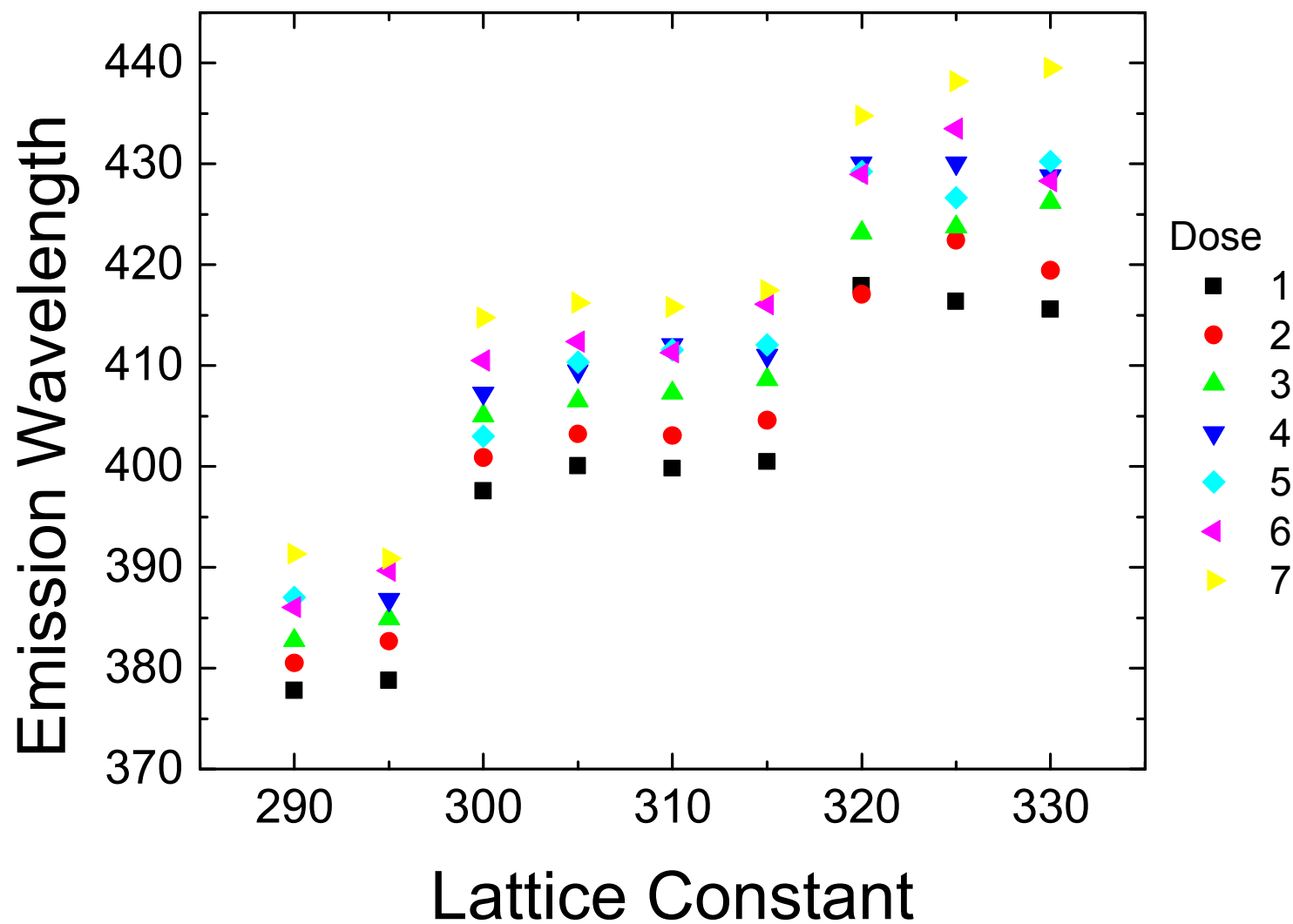
Lu, T.C., et al.. *Applied Physics Letters* **93** (2008).



Kouno, T. et al. *Electron. Lett.* **46** (2010)

Lasing as a function of reduced frequency

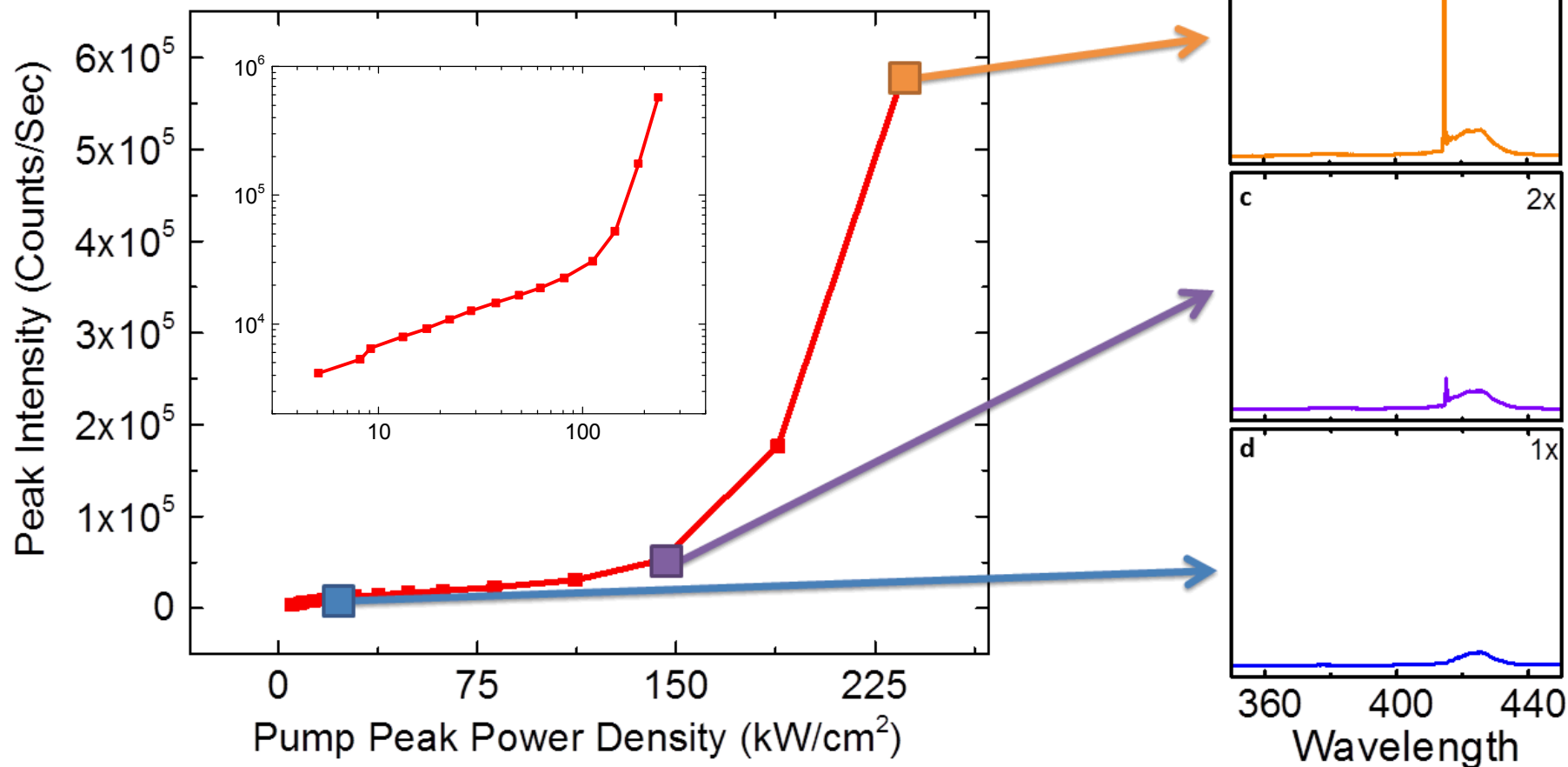




Optical Results from a single array element

a

Array Element Dimensions: $d=143$ nm and $a=320$ nm.



- **Fabricate an array of different color lasers on a single chip that emit vertically with single-mode operation.**
- **Ideal spectral coverage would span the visible wavelengths.**
- **Optical Information Processing, Biology, Solid State Lighting, and Displays**